

Amendments to the Specification (clean):

Replace two paragraphs on Page 6, lines 14-31 with the following text:

Fig. 1A is a perspective view schematically showing a surface emitting laser according to the first embodiment of the invention, and Fig. 1B is a cross-sectional view schematically showing its central part. The surface emitting laser shown here is an improved version VCSEL explained above with reference to Figs. 7A and 7B. That is, HR-DBRs (high-reflectivity distributed Bragg reflectors) 100 (lower) and 200 (upper) of a high reflectivity layer structure are provided on and under an active layer having a MQW (multiple-quantum well) structure on a substrate 1 to make light from the active layer 3 resonate vertically. Laser light, thus obtained, is emitted externally from an opening of a top electrode 50. The semiconductor substrate 1 and the active layer 3 may be formed of semiconductors having a zincblende crystalline structure, such as GaAs, InP, or other suitable III-V semiconductor materials.

In the present invention, side surfaces of the active layer 3 are not normal to the active layer 3, but they are processed to slant in directions gradually increasing in separation as they approach the substrate 1. With these slanted side surfaces, it is ensured to prevent undesirable horizontal resonance and invite vertical resonance alone. These slanted surfaces can be made by processing using HBr-based wet etchant, for example.

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Replace the paragraph on Page 6, line 36 to page 7, line 3 with the following text:

In the illustrated example, side surfaces of the active layer are processed to slant in directions gradually increasing in separation as they approach the substrate 1. However, they may be processed to the contrary, namely, to define slant surfaces gradually decreasing their separation toward the substrate.